Super-mini K-Cell (KC-1300-S)

Features

This is an ultra-small K-cell that is suitable for analysis system.

Specifications

- Maximum heating temperature : 1300℃
- Crucible material : PBN
- Crucible capacity : 2cc
- Mounting flange size : ICF70

Dual K-Cell (DSGC-1400SH)

Features

A single cell port allows the user to use two kinds of materials.

Specifications

- Maximum heating temperature : 1300℃
- Crucible material : PBN
- Crucible capacity : 6cc
- Mounting flange size : ICF152

High Temperature K-Cell for Si (THKC-1000-HI)

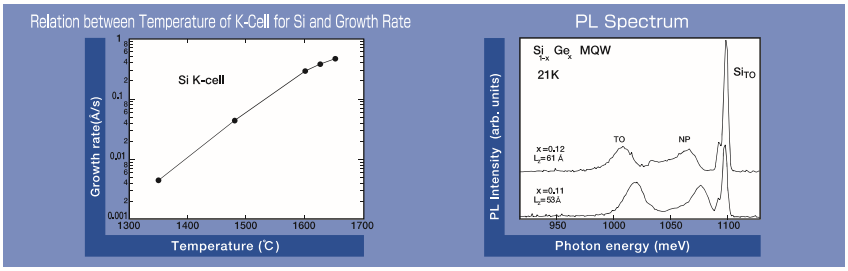
Features

THKC-1000-HI is the world-first K-cell developed for Si, which allows such high precision control of film thickness (0.005-0.5Å/s) as was conventionally impossible by an EB gun.

Specifications

- Maximum heating temperature : 1600℃
- Crucible capacity : 4cc
- Mounting flange size : >ICF70

■Sample of data (High-Temperature K-Cell for Si) Data offered by courtesy of Tokyo University



ECR Radical Cell

Features

ECR Radical Cell adopts a unique mechanism to enable extremely high-density plasma production. The ion removal mechanism (magnetic field system) provided at the top of the cell allows ion removal.

Specifications

- Plasma production system : Microwave (2.45GHz) Discharge type
- Material of plasma chamber : PBN
- Ion removal unit : Magnetic field type
- Mounting flange : >ICF70
- Power supply Microwave supply : 10W to 100W

PL spectrum on h-GaN and c-GaN thin films made by means of the molecular beam epitaxial growth (MBE) method that uses ECR plasma cells, with microwave supply power being 60W and nitrogen flow rate being 1.0 sccm.

■Data offered by courtesy of the Institute of Scientific and Industrial Research, Osaka University